

• General Description

The AGM60P100A combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$

This device is ideal for load switch and battery protection applications.

• Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance
- 100% Avalanche tested
- 100% DVDS tested

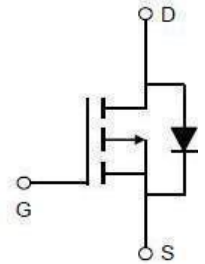
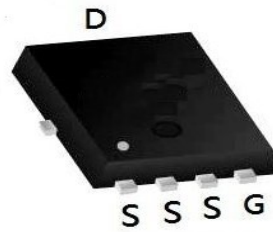
• Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDSON	ID
-60V	5.5mΩ	-140A

PDFN5*6 Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM60P100A	AGM60P100A	PDFN5*6	330mm	12mm	3000

Table 1. Absolute Maximum Ratings (TC=25°C)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	-60	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25°C) (Note 1)	-140	A
	Drain Current-Continuous(Tc=100°C)	-85	A
IDM (pluse)	Drain Current-Continuous@ Current-Pulsed (Note 2)	-560	A
PD	Maximum Power Dissipation(Tc=25°C)	150	w
	Maximum Power Dissipation(Tc=100°C)	60	w
EAS	Avalanche energy (Note 3)	230	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) ¹	---	60	°C/W
RθJC	Thermal Resistance Junction-Case ¹	---	0.83	°C/W

Table 3. Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=-250μA	-60	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=-60V,VGS=0V	--	--	-1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=-250μA	-1.3	-2.0	-2.5	V
gFS	Forward Transconductance	VDS=-10V,ID=-10A	--	36	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=-10V, ID=-15A	--	5.5	6.5	mΩ
		VGS=-4.5V, ID=-10A	--	6.5	9.0	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=-30V,VGS=0V, F=1MHZ	--	3060	--	pF
Coss	Output Capacitance		--	620	--	pF
Crss	Reverse Transfer Capacitance		--	20	--	pF
Rg	Gate resistance	f=1.0MHz	--	2.0	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=-10V,VDS=-30V, ID=-20A, RGEN=3Ω	--	4.5	--	nS
tr	Turn-on Rise Time		--	2.5	--	nS
td(off)	Turn-Off Delay Time		--	14.5	--	nS
tf	Turn-Off Fall Time		--	3.5	--	nS
Qg	Total Gate Charge	VGS=-10V, VDS=-30V, ID=-15A	--	56	--	nC
Qgs	Gate-Source Charge		--	11	--	nC
Qgd	Gate-Drain Charge		--	9	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	-140	A
VSD	Forward on Voltage	VGS=0V,IS=-15A	--	--	-1.2	V
trr	Reverse Recovery Time	Isd=-15A ,	--	60	--	ns
Qrr	Reverse Recovery Charge	dI/dt=100A/μs , T _J =25°C	--	105	--	nc

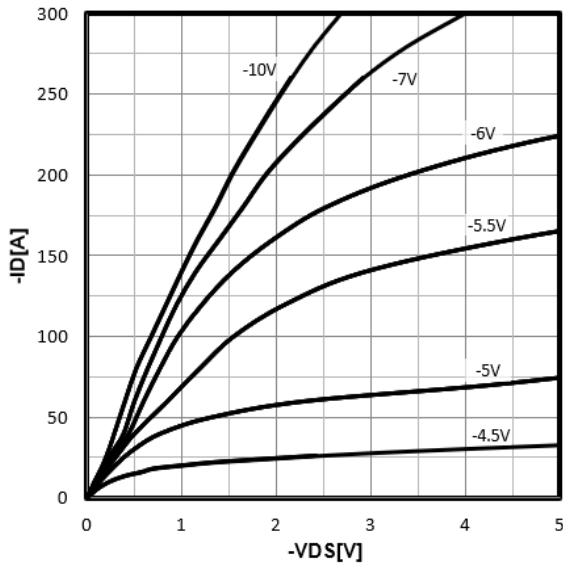
Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

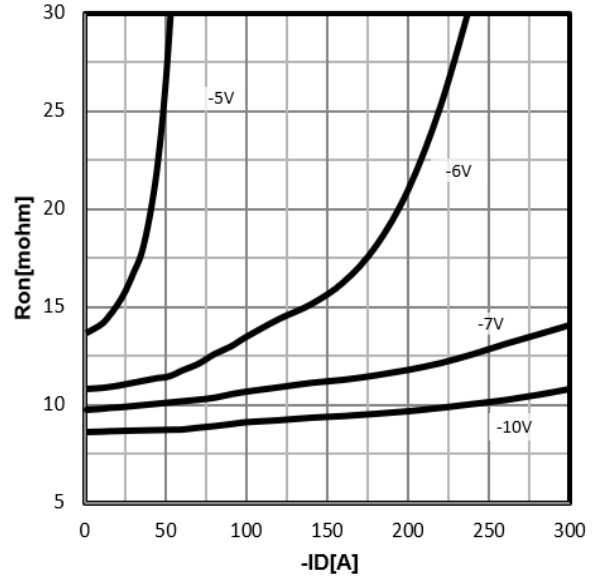
Notes 3.EAS condition: T_J=25°C

Characteristics Curve:
Typ. output characteristics

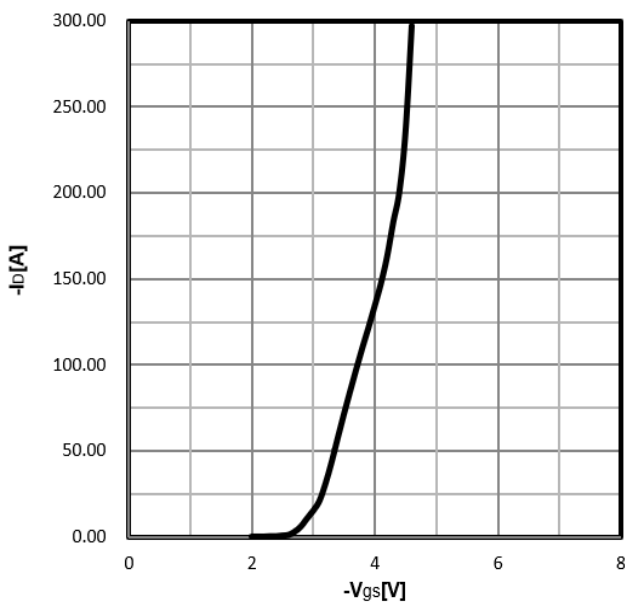
$$I_D = f(V_{DS})$$


Typ. drain-source on resistance

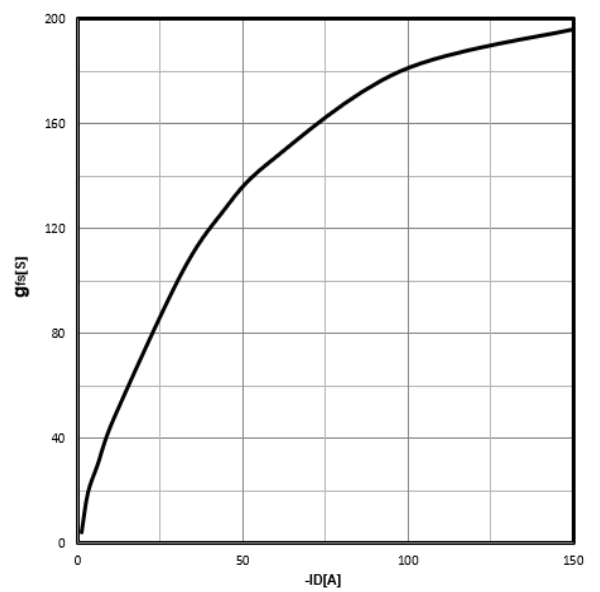
$$R_{DS(on)} = f(I_D)$$


Typ. transfer characteristics

$$I_D = f(V_{GS})$$

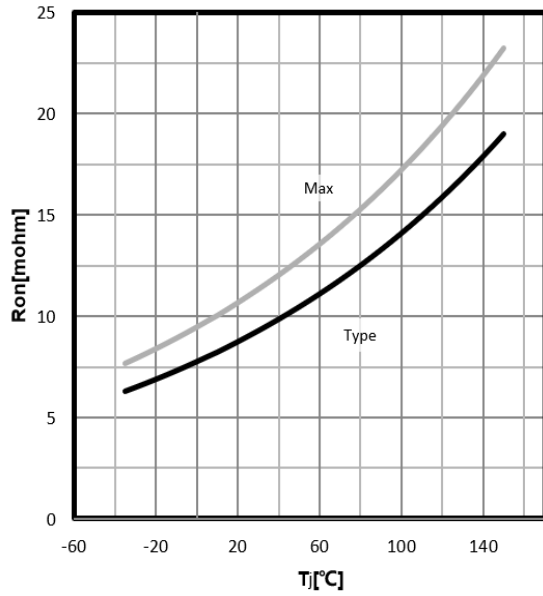

Typ. forward transconductance

$$g_{fs} = f(I_D)$$

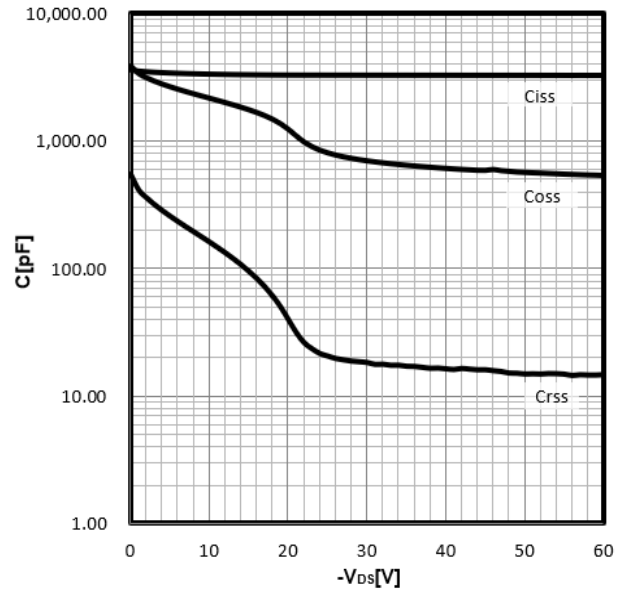


Drain-source on-state resistance

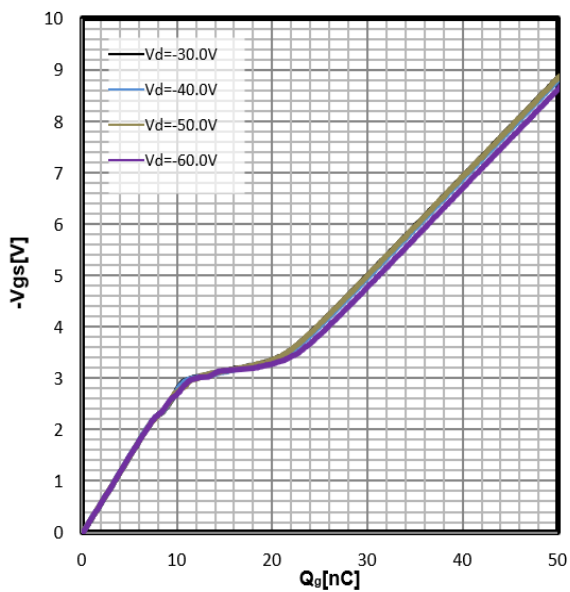
$$R_{DS(on)} = f(T_j); I_D = -20A; V_{GS} = -10V$$


Typ. capacitances

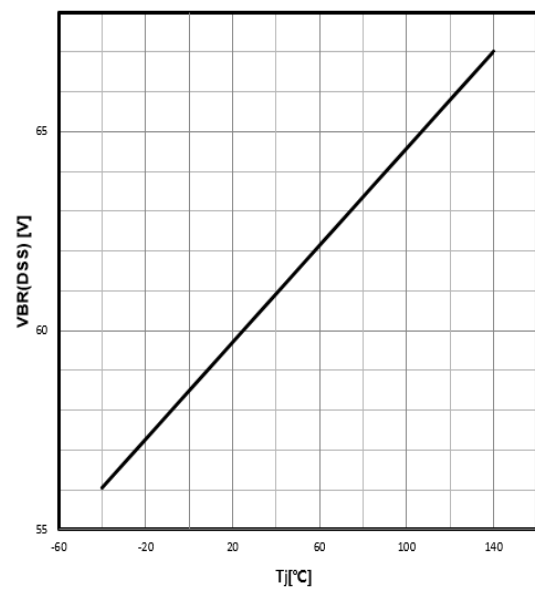
$$C = f(V_{DS}); V_{GS} = 0V; f = 1MHz$$


Typ. gate charge

$$V_{GS} = f(Q_{gate}); I_D = -20A$$

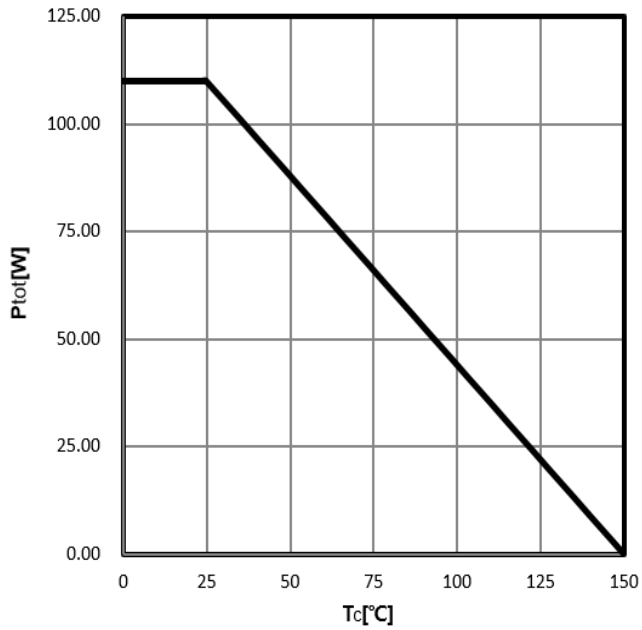

Drain-source breakdown voltage

$$V_{BR(DSS)} = f(T_j); I_D = -250\mu A$$

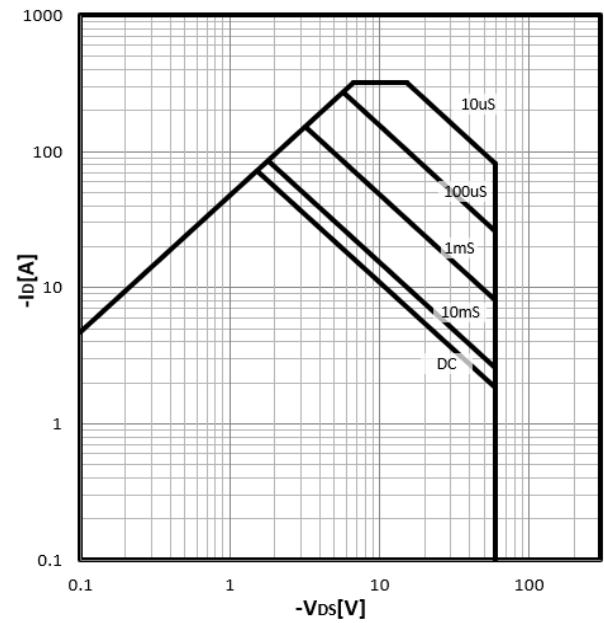


Power Dissipation

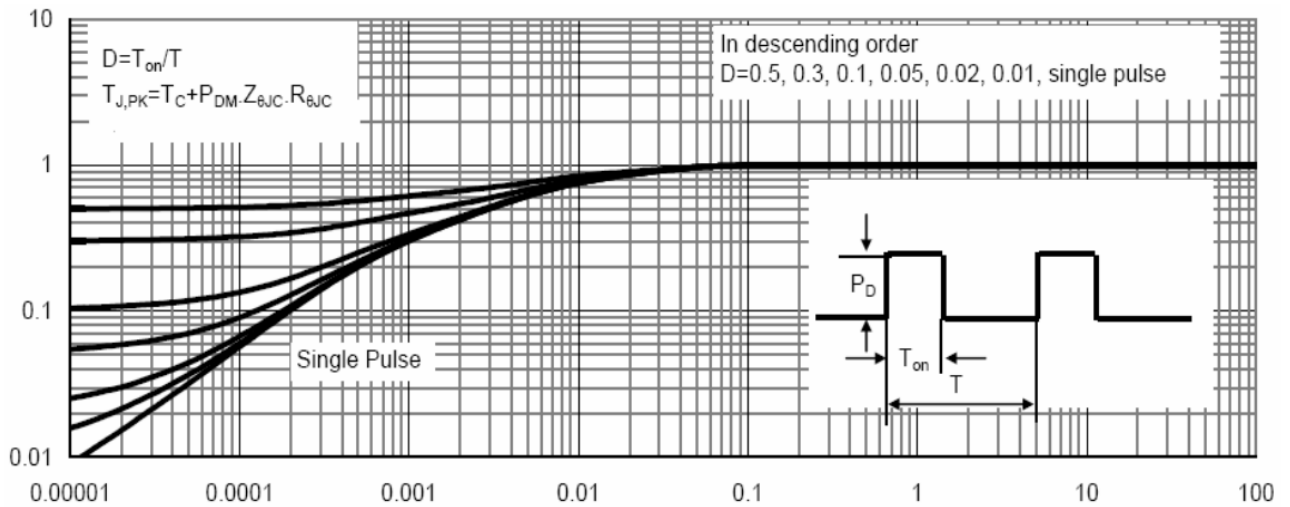
$$P_{tot}=f(T_c)$$

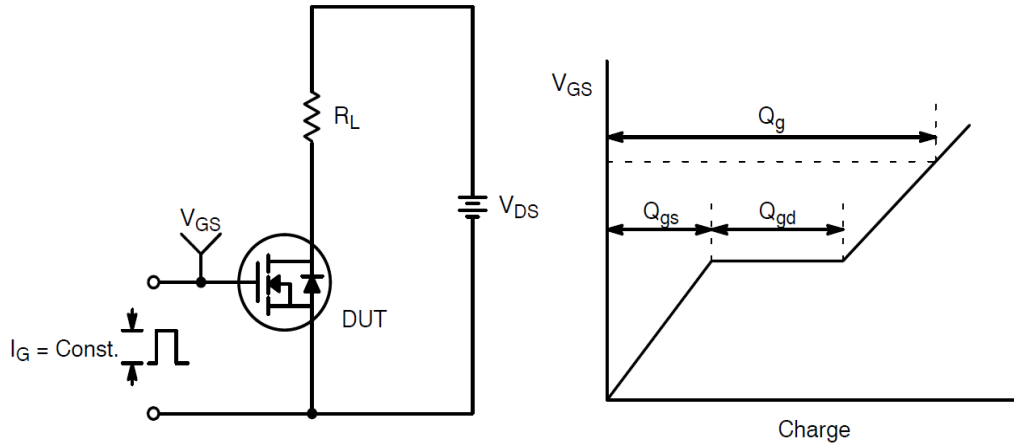
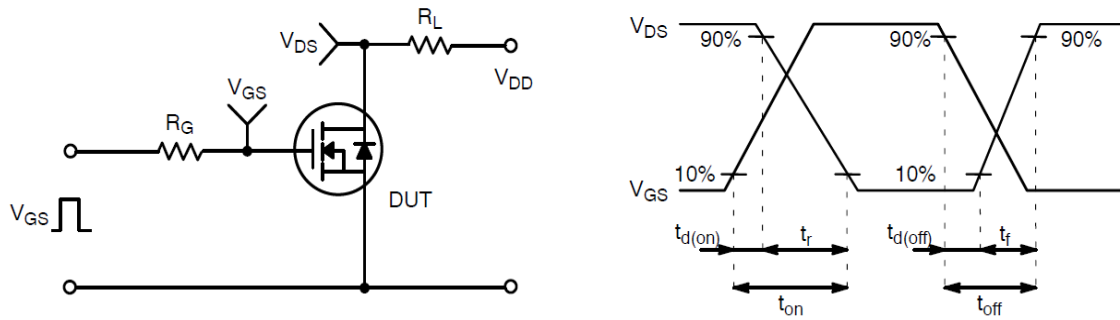
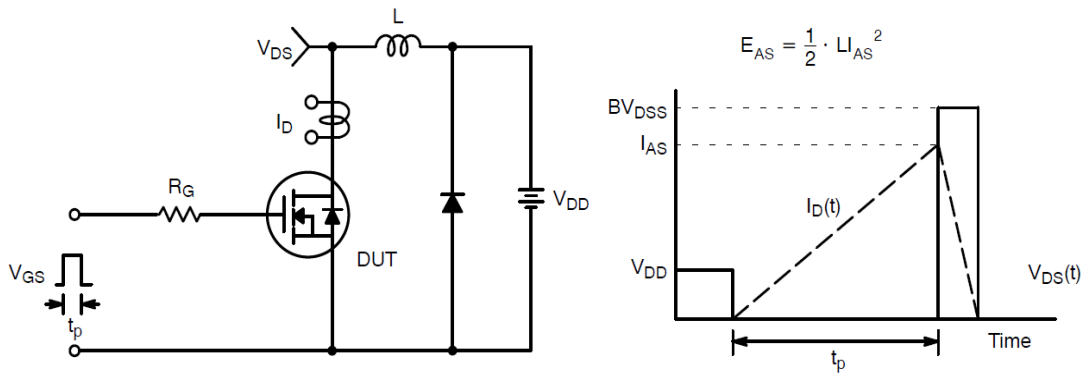

Safe operating area

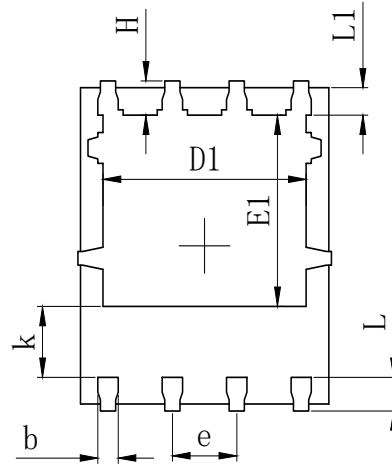
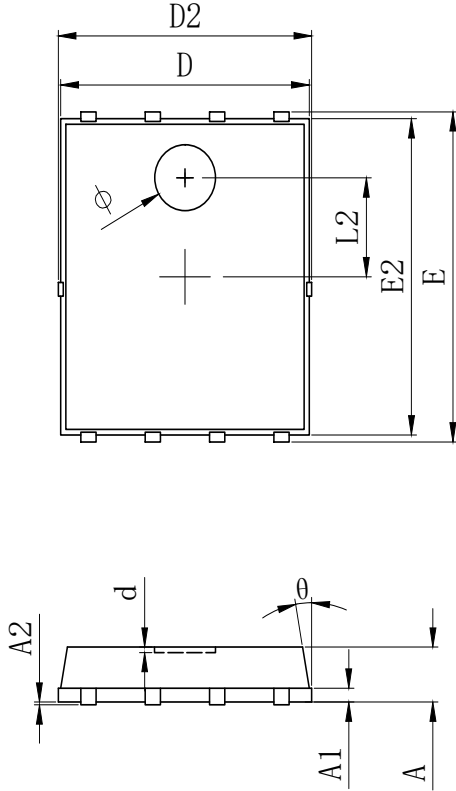
$$I_D=f(V_{DS})$$


Max. transient thermal impedance

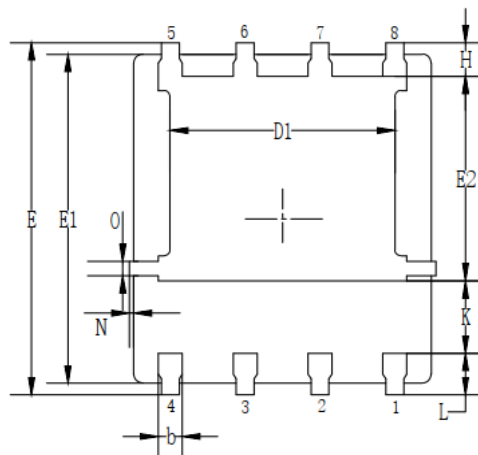
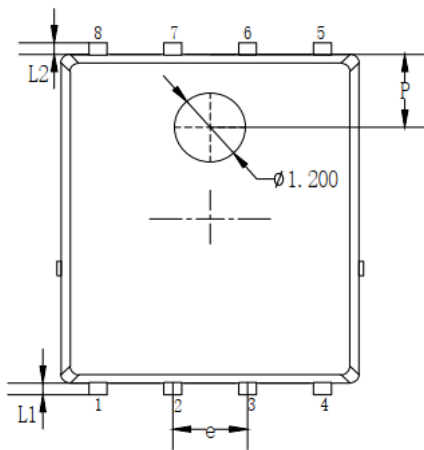
$$Z_{thJC}=f(t_p)$$



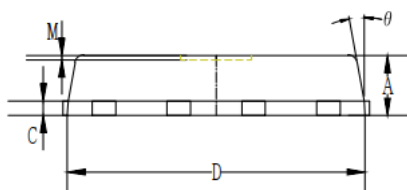
Test Circuit and Waveform:

Gate Charge Test Circuit & Waveform

Resistive Switching Test Circuit & Waveforms

Unclamped Inductive Switching Test Circuit & Waveforms

•Dimensions (PDFN5*6)


SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	0.900	1.000	1.100
A1	0.254 REF.		
A2	0°0.05		
D	4.824	4.900	4.976
D1	3.910	4.010	4.110
D2	4.924	5.000	5.076
E	5.924	6.000	6.076
E1	3.375	3.475	3.575
E2	5.674	5.750	5.826
b	0.350	0.400	0.450
e	1.270 TYP.		
L	0.534	0.610	0.686
L1	0.424	0.500	0.576
L2	1.800 REF.		
k	1.190	1.290	1.390
H	0.549	0.625	0.701
θ	8°	10°	12°
φ	1.100	1.200	1.300
d			0.100



Symbols	Millimeters		
	MIN.	NOM.	MAX.
A	0.90	1.05	1.20
b	0.35	0.40	0.50
c	0.20	0.25	0.35
D	4.90	5.05	5.20
D1	3.72	3.82	3.92
E	6.00	6.15	6.30
E1	5.60	5.75	5.90
E2	3.47	3.57	3.67
e	1.27 BSC.		
H	0.48	0.58	0.68
K	1.17	1.27	1.37
L	0.64	0.74	0.84
L1/L2	0.20 REF.		
θ	8°	10°	12°
M	0.08 REF.		
N	0	-	0.15
O	0.25 REF.		
P	1.28 REF.		




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